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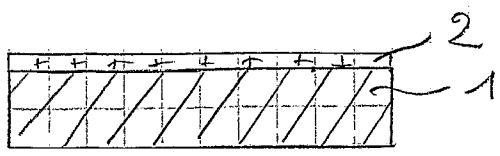
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(54) Title: METHOD OF MANUFACTURING A SILICON DIOXIDE LAYER



(57) Abstract: The invention relates to a of manufacturing a silicon dioxide layer (2) of low roughness, comprising the step of: - depositing a layer of silicon dioxide (2) over a substrate (1) by a low pressure chemical vapour deposition (LPCVD) process, the deposition process employing simultaneously a flow of tetraethylorthosilicate (TEOS) as the source material for the film deposition and a flow of a diluant gas that it not reactive with TEOS, so that the diluant gas / TEOS flow ratio is between 0.5 and 100; - annealing said silicon dioxide layer at a temperature between 600°C and 1200°C, for a duration between 10 minutes and 6 hours.

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